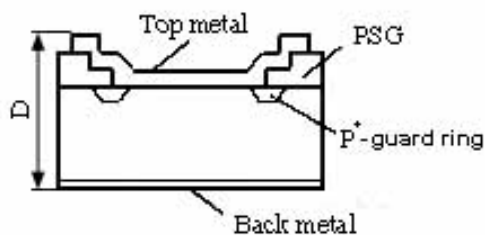
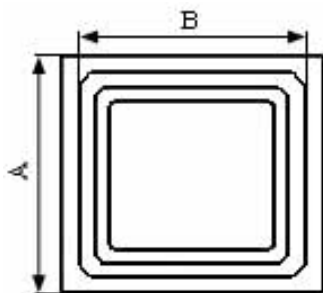


		15A/45V. Die Size-120mil.		
Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort
Breakdown Voltage @ $I_R=10mA$	$V_{BR}$	V	45	50
Average Rectified Forward Current	$I_{F(AV)}$	A	15,0	-
DC Forward Voltage @ 25°C, $I_F=15,0A$	$V_F$	V	0.52	0.50
Maximum Reverse Current @ 25°C, $V_R=50V$ @ 25°C, $V_R=45V$ @ 125°C, $V_R=45V$	$I_R$	mA	- 0,100 80,0	0,100 0,060 75,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	$I_{FSM}^*$	A	250	-
Peak Repetitive Reverse Surge Current @2,0µs, $f=1kHz.$ , $T_J<150°C$ .	$I_{RRM}$	A	4,5	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	±8 (contact)	
Voltage Rate of Change	$dV/dt$	V/µS	10.000	
Operating Junction Temperature	$T_J^{**}$	°C	150	

\* - testing for Device

\*\* -  $T_J = T_a + R_{th}(j-a) \times (P_f + P_r)$ , where  $R_{th}(j-a)$  – thermal resistance,  $P_f$  – forward power dissipation,  $P_r$  – revers power dissipation



DIM	ITEM	µm
$A_x$ $A_y$	Wafer Form Die Size	3050
$B_x$ $B_y$	Top Metal Size	2930
D	Thickness	300max.
Scribe line Width		80

Top metal:

- a) Al – for Wire Bonding;
  - b) Al-Ni-Ag – for Soldering.
- Backside metal: Ti-Ni-Ag.